

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	1336	phase adj5 change adj5 memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 10:33
L3	20	2 same chalcogenic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 11:00
L4	5	3 same (control or controller or controll\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 10:59
L5	8	("4599705" "4876668" "5801983" "5883827" "5898619" "6314014" "6590807" "6673648").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/10/15 10:38
L6	75	(phase adj5 change adj5 storage) same array	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 10:40
L9	42	2 and 6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 10:41
L11	17	9 and @ad<"20021118"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 10:50
L12	96	2 and temperatur\$2 and bias and array	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 10:46

L13	45	12 and "365"/\$7.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 10:46
L14	11	13 and @ad<"20021118"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 10:46
L20	49	device and chalcogenic\$2 and control	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 10:54
L21	40	20 and temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 10:52
L22	10	21 and resistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 10:53
L25	302	2: same (control or controller or controll\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 10:56
L26	53	25 same temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 10:56
L27	20	26 and "365"/\$7.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 10:56

L29	10	26 and "365"/163,148.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 10:57
L30	100	2 and 365/163;164,148.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 10:59
L31	5	30 and chalcogenic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 11:00
L34	2	"20010009528"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 11:04
L35	49	khouri-osama.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 11:04
L36	20	bedeschi-ferdinando.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 11:04
L37	16	resta-claudio.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 11:04
L38	1	(device and chalcogenic and (control adj3 circuit) and temperature and (resistor or resistance or resistive)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 11:06

L40	1	(method and temperature and device and chalcogenic and (detect\$3 or detector\$2) and (resistor or resistance or resistiv\$2) and (control or controller or controll\$3)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 11:08
L41	1	(memory and array and (phase adj3 change adj3 memory) and chalcogenic and (control or controller or controll\$3) and temperatur\$2 and (resistor or resistance or resistiv\$2)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 11:09